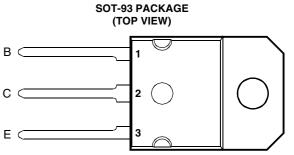
BD249, BD249A, BD249B, BD249C NPN SILICON POWER TRANSISTORS

BOURNS®

- Designed for Complementary Use with the BD250 Series
- 125 W at 25°C Case Temperature
- 25 A Continuous Collector Current
- 40 A Peak Collector Current
- Customer-Specified Selections Available



Pin 2 is in electrical contact with the mounting base.

absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING			VALUE	UNIT	
	BD249		55		
Collector omitter veltage $(P_{1} = 100.0)$	BD249A	V	70	v	
Collector-emitter voltage ($R_{BE} = 100 \Omega$)	BD249B	V _{CER}	90	v	
	BD249C		115		
Collector-emitter voltage (I _C = 30 mA)	BD249		45		
	BD249A	V	60	v	
	BD249B	V _{CEO}	80	v	
	BD249C		100		
Emitter-base voltage			5	V	
Continuous collector current			25	A	
Peak collector current (see Note 1)		I _{CM}	40	A	
Continuous base current			5	A	
Continuous device dissipation at (or below) 25°C case temperature (see Note 2)			125	W	
Continuous device dissipation at (or below) 25°C free air temperature (see Note 3)			3	W	
Unclamped inductive load energy (see Note 4)			90	mJ	
Operating junction temperature range			-65 to +150	°C	
Storage temperature range			-65 to +150	°C	
Lead temperature 3.2 mm from case for 10 seconds			250	°C	

NOTES: 1. This value applies for $t_p \leq 0.3$ ms, duty cycle $\leq 10\%.$

2. Derate linearly to 150°C case temperature at the rate of 1 W/°C.

3. Derate linearly to 150°C free air temperature at the rate of 24 mW/°C.

4. This rating is based on the capability of the transistor to operate safely in a circuit of: L = 20 mH, $I_{B(on)}$ = 0.4 A, R_{BE} = 100 Ω , $V_{BE(off)}$ = 0, R_S = 0.1 Ω , V_{CC} = 20 V.

PRODUCT INFORMATION

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electrical characteristics at 25°C case temperature

	PARAMETER		TEST CONDITION	ONS	MIN	ТҮР	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C = 30 mA (see Note 5)	I _B = 0	BD249 BD249A BD249B	45 60 80			V
I _{CES}	Collector-emitter cut-off current	$V_{CE} = 55 V$ $V_{CE} = 70 V$ $V_{CE} = 90 V$ $V_{CE} = 115 V$	$V_{BE} = 0$ $V_{BE} = 0$ $V_{BE} = 0$ $V_{BE} = 0$	BD249C BD249 BD249A BD249B BD249B BD249C	100		0.7 0.7 0.7 0.7	mA
I _{CEO}	Collector cut-off current	$V_{CE} = 30 V$ $V_{CE} = 60 V$	I _B = 0 I _B = 0	BD249/249A BD249B/249C			1 1	mA
I _{EBO}	Emitter cut-off current	V _{EB} = 5 V	I _C = 0				1	mA
h _{FE}	Forward current transfer ratio	$V_{CE} = 4 V$ $V_{CE} = 4 V$ $V_{CE} = 4 V$	I _C = 1.5 A I _C = 15 A I _C = 25 A	(see Notes 5 and 6)	25 10 5			
V _{CE(sat)}	Collector-emitter saturation voltage	$I_B = 1.5 A$ $I_B = 5 A$	I _C = 15 A I _C = 25 A	(see Notes 5 and 6)			1.8 4	V
V _{BE}	Base-emitter voltage	$V_{CE} = 4 V$ $V_{CE} = 4 V$	I _C = 15 A I _C = 25 A	(see Notes 5 and 6)			2 4	V
h _{fe}	Small signal forward current transfer ratio	V _{CE} = 10 V	I _C = 1 A	f = 1 kHz	25			
h _{fe}	Small signal forward current transfer ratio	V _{CE} = 10 V	I _C = 1 A	f = 1 MHz	3			

NOTES: 5. These parameters must be measured using pulse techniques, $t_p = 300 \ \mu s$, duty cycle $\leq 2\%$.

6. These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

thermal characteristics

PARAMETER			ТҮР	MAX	UNIT
R _{θJC}	Junction to case thermal resistance			1	°C/W
R _{θJA}	Junction to free air thermal resistance			42	°C/W

resistive-load-switching characteristics at 25°C case temperature

PAR	AMETER	TEST CONDITIONS [†]			MIN	ТҮР	MAX	UNIT
t _{on} Tur	rn-on time	I _C = 5 A	I _{B(on)} = 0.5 A	$I_{B(off)} = -0.5 A$		0.3		μs
t _{off} Tur	rn-off time	$V_{BE(off)} = -5 V$	$R_L = 5 \Omega$	t_p = 20 µs, dc \leq 2%		0.9		μs

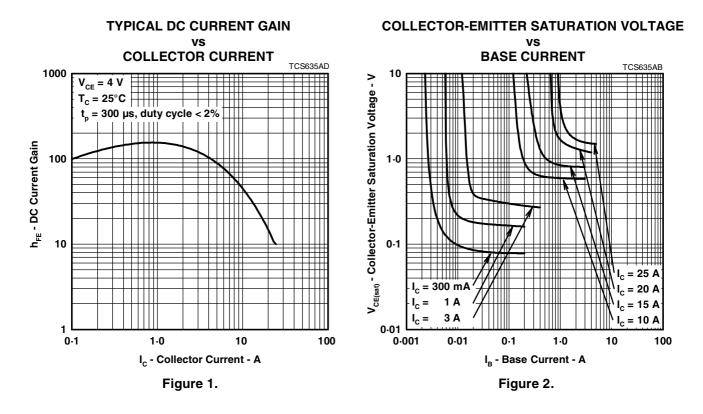
[†] Voltage and current values shown are nominal; exact values vary slightly with transistor parameters.





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TYPICAL CHARACTERISTICS

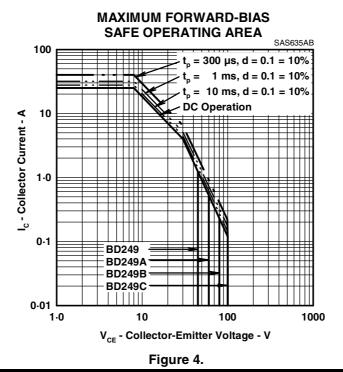


BASE-EMITTER VOLTAGE vs **COLLECTOR CURRENT** TCS635AC 2.0 $V_{CE} = 4 V$ T_c = 25°C 1.8 V_{BE} - Base-Emitter Voltage - V 1.6 1.4 1.2 1.0 0.8 0.6 0.1 1.0 10 100 I_c - Collector Current - A Figure 3.

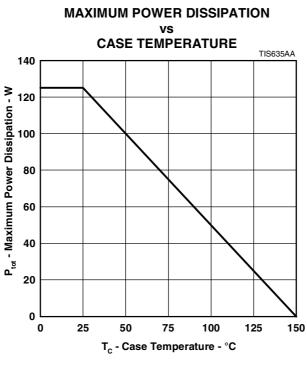
PRODUCT INFORMATION

JUNE 1973 - REVISED SEPTEMBER 2002 Specifications are subject to change without notice.

MAXIMUM SAFE OPERATING REGIONS









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